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FITZPATRICK CELLA HARPER & SCINTO 30 ROCKEFELLER PLAZA NEW YORK, NY 10112			JONÉS, HEATHER RAE	
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			2621	

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Please find below and/or attached an Office communication concerning this application or proceeding.

DETAILED ACTION

Response to Arguments

1. Applicant's arguments with respect to claims 1-9 have been considered but are moot in view of the new ground(s) of rejection.

Claim Rejections - 35 USC § 103

2. The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.
3. Claims 1, 5, and 8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shintani et al. (U.S. Patent 5,875,034) in view of the admitted prior art, and further in view of Ackland et al. ("Camera on a Chip").

Regarding claim 1, Shintani et al. teaches a sensor comprising a sensor block (CCD) including a pixel unit comprising a plurality of pixels each including a light-receiving element and a signal processing block (signal processing unit 102) for processing a signal output from said sensor block (col. 7, lines 26-31). As the CCD outputs pixel information to the signal processing block, a scanning unit for selecting a pixel of said pixel unit is inherently taught. Shintani et al. teaches a single electric power voltage input terminal for externally inputting an external power voltage (main battery EB in power supply unit 109) from outside of the sensor (Fig. 2A, col. 7, 56-58); and a voltage supply unit for supplying a first voltage to the sensor block, and for supplying a second voltage to the signal processing block, wherein the second voltage is smaller in amplitude than the

first voltage, and wherein the voltage supply unit is supplied with electric power from a single power source disposed externally of the semiconductor substrate (main battery EB in power supply unit 109) (col. 7, lines 52-55; col. 9, lines 7-25). Shintani et al. teaches that the power supply unit 109 is adapted for supplying a high voltage of a predetermined level to the CCD 101, and a lower voltage of a predetermined level to other individual circuit elements (col. 7, lines 52-55), which reads on a power supply voltage used in a sensor block that is higher than a power supply voltage supplied to another individual circuit element. However, Shintani et al. fails to teach that the sensor is integrated on a single semiconductor substrate and that the control circuit is arranged on the substrate.

Referring to the admitted prior art, the admitted prior art teaches a sensor integrated on a single semiconductor substrate (page 1, lines 10-12).

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the practice of fabricating camera elements on a single integrated chip taught by the admitted prior art into the camera of Shintani et al. One of ordinary skill would have been motivated to make such a modification to shorten the time needed to transport pixel data from the image sensor to the signal processing unit. However, Shintani et al. in view of the admitted prior art still fails to teach that the control circuit is arranged on the substrate.

Referring to the Ackland et al. reference, Ackland et al. discloses a camera wherein the control circuit is arranged on the main substrate along with

the other components (Page 23, col. 1, paragraph 5, line 8 – col. 2, paragraph 2, line 3; Page 24, col. 1, paragraph 5, lines 1-2; Fig. 7).

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to have used the teaching of arranging the control circuit onto the main substrate with the other components as taught by Ackland et al. in the camera system disclosed by Shintani et al. in view of the admitted prior art in order to provide a device that has a substantially lower power consumption and a higher expected reliability, due to the reduced number of external connections.

Regarding claim 5, Shintani et al. in view of the admitted prior art and in view of Ackland et al. discloses all the subject matter as discussed with respect to claim 1 as well as the admitted prior art teaches that the light-receiving element is a buried photodiode (page 2, line 5). One of ordinary skill would have been motivated to use the buried photodiode of the admitted prior art in the sensor of Shintani et al. to obtain a signal with a higher S/N ratio.

Regarding claim 8, Shintani et al. in view of the admitted prior art and in view of Ackland et al. discloses all the subject matter as discussed with respect to claim 1 as well as Shintani et al. teaches an A/D converter for converting the signal (Fig. 4A, item 305). It would have been obvious to one of ordinary skill to incorporate the A/D conversion into the signal-processing block.

4. Claim 2 is rejected under 35 U.S.C. 103(a) as being unpatentable over Shintani et al. in view of the admitted prior art in view of Ackland et al. as applied to claim 1 above, and further in view of Mann et al. (U.S. Patent 6,121,087).

Regarding claim 2, Shintani et al. in view of the admitted prior art in view of Ackland et al. teach the apparatus of claim 1. See above. Shintani et al. in view of the admitted prior art in view of Ackland et al. do not teach that a gate insulating layer of at least some insulated gate transistors of said sensor block is thicker than that of an insulated gate transistor used in said signal processing block. Mann et al. teaches that the application of a higher voltage will require a thicker gate oxide layer to prevent oxide-breakdown (col. 6, lines 34-42). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the practice of growing a thicker oxide when a higher voltage is being applied taught by Mann et al. into the apparatus of Shintani et al. in view of the admitted prior art in view of Ackland et al. to make an image sensing apparatus that uses a higher power voltage, and thus thicker gate oxide layers, for the sensor block and a lower power voltage, and thus thinner gate oxide layers, for the signal processing block. One of ordinary skill would have been motivated to make such a modification to fabricate the appropriate thickness of oxide for the voltage that shall be used upon it.

5. Claim 3 is rejected under 35 U.S.C. 103(a) as being unpatentable over Shintani et al. in view of the admitted prior art in view Ackland et al. in view of Mann et al. as

Art Unit: 2621

applied to claims 1 and 2 above, and further in view of Sawada et al. (U.S. Patent 6,184,516).

Regarding claim 3, Shintani et al. in view of the admitted prior art in view of Ackland et al. teach the apparatus of claim 1. See above. Shintani et al. in view of the admitted prior art in view of Ackland et al. in view of Mann et al. teach that the threshold voltages for the sensor block transistors are higher than the threshold voltages for the signal processing block transistors. See above.

Shintani et al. in view of the admitted prior art in view of Ackland et al. in view of Mann et al. do not teach that the well density of at least some insulated gate transistors of said sensor block is lower than that of an insulated gate transistor used in said signal processing block. Sawada et al. teaches a PMOS transistor 323 is formed on an n type well 19 whose impurity concentration is higher than that of the n type semiconductor substrate on which the n type well 19 is formed, and a PMOS transistor 324 is formed outside of the n type well 19 on the n type semiconductor substrate. The threshold voltage of PMOS transistor 323 formed on the n type well 19 is about -0.75 V, and that the threshold voltage of the PMOS transistor 324 formed outside of the n type well on the n type semiconductor substrate is about -0.29V (col. 6, line 61 - col. 7, line 8).

Therefore, Sawada et al. teaches that the transistor formed in a substrate possessing a lower well impurity concentration will have a higher threshold voltage. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the teaching of fabricating a

transistor in a substrate with a lower impurity concentration to achieve a higher threshold voltage taught by Sawada et al. with the apparatus of Shintani et al. in view of the admitted prior art in view of Ackland et al. in view of Mann et al. to make an image sensing apparatus whose signal processing block transistors use lower voltage, possess thinner gate oxide layers, and are fabricated in wells of lower impurity concentration than those of the transistors on the signal processing block. One of ordinary skill would have been motivated to make such a modification to reduce the overall power consumption of the chip.

6. Claim 4 is rejected under 35 U.S.C. 103(a) as being unpatentable over Shintani et al. in view of the admitted prior art in view of Ackland et al. in view of Mann et al. as applied to claims 1 and 2 above, and further in view of Gardner et al. (U.S. Patent Application Publication 2002/0022325).

Regarding claim 4, Shintani et al. in view of the admitted prior art in view of Ackland et al. teach the apparatus of claim 1. See above. Shintani et al. in view of the admitted prior art in view of Ackland et al. in view of Mann et al. teach that the gate insulating layers of some transistors of said sensor block is thicker than that of an insulated gate transistor used in said signal processing block. See claim 2 above. Shintani et al. in view of the admitted prior art in view of Ackland et al. in view of Mann et al. do not teach that a threshold voltage of at least some insulated gate transistors of said sensor block is higher than that of an insulated gate transistor used in said signal processing block. Gardner et al. teaches that thinner gate oxides will require a lower threshold voltage [0008]. Therefore, it

Art Unit: 2621

would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the teaching of having a lower threshold voltage when a transistor has a thinner gate oxide taught by Gardner et al. into the apparatus of Shintani et al. in view of the admitted prior art in view of Ackland et al. in view of Mann et al. to make an image sensing apparatus whose transistors in the signal processing block use a lower power supply and possess a lower threshold voltage than the transistors on the signal processing block. One of ordinary skill would have been motivated to make such a modification to reduce the power consumption of the sensor block by using different power supplies and reduce the fabrication time by growing thinner oxides that require lower threshold voltages.

7. Claim 6 is rejected under 35 U.S.C. 103(a) as being unpatentable over Shintani et al. in view of the admitted prior art in view of Ackland et al. as applied to claims 1 and 5 above, and further in view of Tandon et al. (EP 0 254 497).

Regarding claim 6, Shintani et al. in view of the admitted prior art in view of Ackland et al. teach the apparatus of claim 5. See above. Shintani et al. in view of the admitted prior art in view of Ackland et al. do not teach that each pixel has a charge/voltage conversion unit connected to the buried photodiode through a transfer switch. Tandon et al. does teach that each pixel has a charge/voltage conversion unit (source follower 33) connected to a photodiode (14) through a transfer switch (phi. 1) (col. 3, lines 25-32). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to

incorporate the charge/voltage conversion unit and transfer switches of Tandon et al. into the apparatus of Shintani et al. in view of the admitted prior art in view of Ackland et al. to make an image sensing apparatus that uses a lower power supply for the signal processing block than the sensor and converts the photoelectric charge accumulated in the pixels into voltage when the charge is transferred. One of ordinary skill would have been motivated to make such a modification to control when the charges are transferred and converted to voltages.

8. Claim 7 is rejected under 35 U.S.C. 103(a) as being unpatentable over Shintani et al. in view of the admitted prior art in view of Ackland et al. as applied to claim 1 above, and further in view of Vu et al. (U.S. Patent 6,025,875).

Regarding claim 7, Shintani et al. in view of the admitted prior art in view of Ackland et al. teach the apparatus of claim 1. See above. Shintani et al. in view of the admitted prior art in view of Ackland et al. do not teach that the sensor block and signal processing block are connected via a level shift circuit for shifting a signal level. Vu et al. teaches that the sensor block and signal processing block are connected via level shift circuit (coupling capacitor C_{CL}) for shifting a signal level (col. 4, lines 9-13). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the level shift circuit of Vu et al. into the apparatus of Shintani et al. in view of the admitted prior art in view of Ackland et al. to make an image sensing apparatus that supplies different voltages to the CCD and signal processor and

Art Unit: 2621

uses a level shift circuit or shifting a signal level between the CCD and signal processor. One of ordinary skill would have been motivated to make such a modification to reduce signals' voltage level when they are to enter another functional unit that employs a lower voltage supply.

9. Claim 9 is rejected under 35 U.S.C. 103(a) as being unpatentable over Shintani et al. in view of the admitted prior art in view of Ackland et al. as applied to claims 1 and 8 above, and further in view of well-known prior art.

Regarding claim 9, Shintani et al. in view of the admitted prior art in view of Ackland et al. teach the apparatus of claim 8. See above. Although Shintani et al. in view of the admitted prior art in view of Ackland et al. do not teach a circuit for forming a luminance signal and a chrominance signal, the office takes Official Notice that it would have been obvious to one of ordinary skill in the art at the time the invention was made to separate the image data of Shintani et al. in view of the admitted prior art in view of Ackland et al. into luminance and chrominance signals. One of ordinary skill would have been motivated to make such a modification to convert the image data into a format that is commonly used in signal processing methods.

Conclusion

10. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP

§ 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Heather R. Jones whose telephone number is 571-272-7368. The examiner can normally be reached on Mon. - Thurs.: 7:00 am - 4:30 pm, and every other Fri.: 7:00 am - 3:30 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thai Tran can be reached on 571-272-7382. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

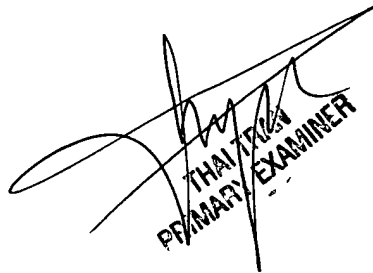
For any written or facsimile communication submitted on or after March 22, 2006, the Examiner, who was assigned to Art Unit 2616, will be assigned to the new Art Unit 2621. Please include the new Art Unit in the caption or heading of any communication submitted after March 22, 2006. Your cooperation in this matter will assist in the timely processing of the submission and is appreciated by the Office.

Art Unit: 2621

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Heather R Jones
Examiner
Art Unit 2621

HRJ
March 31, 2006



THAI TONG
PRIMARY EXAMINER